## THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-Case	Max	1.78	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-Ambient	Max	70	°C/W

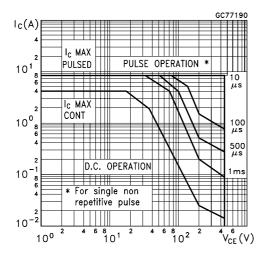
# **ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25 \ ^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
ICES	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 850 V V <sub>CE</sub> = 850 V	T <sub>j</sub> = 125 °C			100 500	μΑ μΑ
I <sub>EBO</sub>	Emitter Cut-off Current $(I_C = 0)$	V <sub>EB</sub> = 9 V				100	μA
$V_{CEO(sus)^*}$	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA	L = 25 mH	450			V
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1 A I <sub>C</sub> = 2.5 A	I <sub>B</sub> = 0.2 A I <sub>B</sub> = 0.5 A		0.13	0.5 1.1	V V
$V_{BE(sat)^*}$	Base-Emitter Saturation Voltage	$I_{C} = 1 A$ $I_{C} = 2.5 A$	I <sub>B</sub> = 0.2 A I <sub>B</sub> = 0.5 A			1.1 1.3	V V
h <sub>FE</sub> *	DC Current Gain	$I_{C} = 5 A$ $I_{C} = 10 mA$	V <sub>CE</sub> = 10 V V <sub>CE</sub> = 5 V	4 10			
V <sub>CEW</sub>	Maximum Collector Emitter Voltage Without Snubber	$I_{C} = 6 A$ $V_{BB} = -2.5 V$ $t_{p} = 10 \ \mu s$	R <sub>BB</sub> = 0 Ω L = 50μH	450			V
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	$I_{C} = 2.5 \text{ A}$ $V_{BE(off)} = -5 \text{ V}$ $V_{CL} = 300 \text{ V}$	$I_{B(on)} = 0.5 A$ $R_{BB} = 0 \Omega$ L = 1 mH		0.7 50	1.5 100	μs ns
Vf	Diode Forward Voltage	I <sub>C</sub> = 2 A				1.5	V

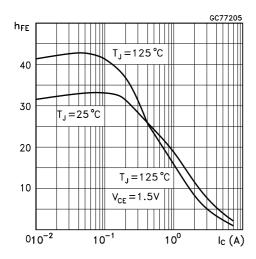
57

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

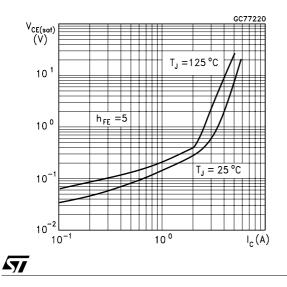
#### Safe Operating Areas



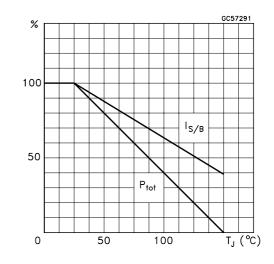
#### DC Current Gain



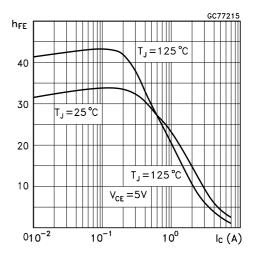
#### Collector Emitter Saturation Voltage

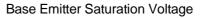


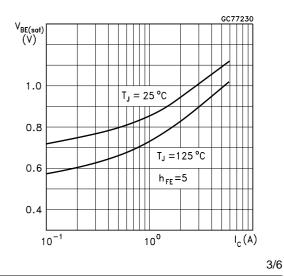
#### **Derating Curve**



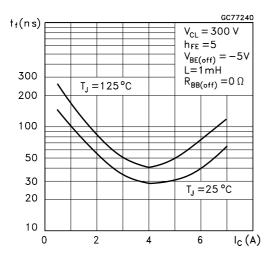
## DC Current Gain



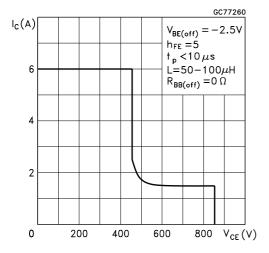




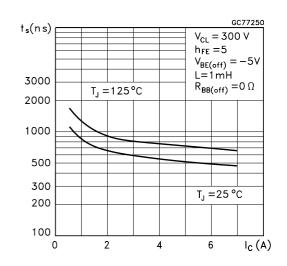
#### Inductive Fall Time



#### **Reverse Biased SOA**



Inductive Storage Time

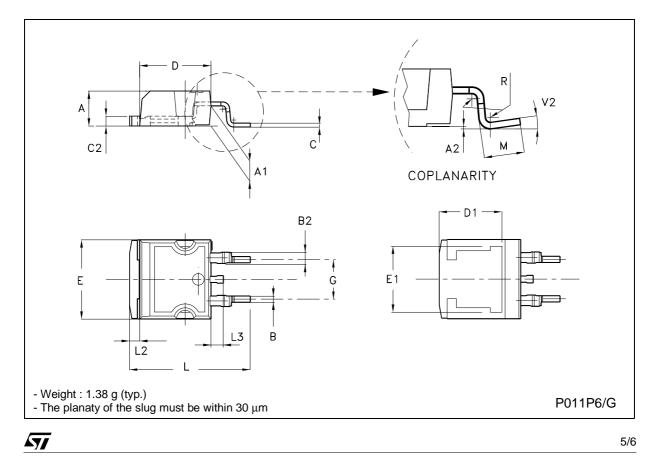


57

4/6

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.40		4.60	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.70		0.93	0.027		0.036
B2	1.14		1.70	0.044		0.067
С	0.45		0.60	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8.00			0.315	
Е	10.00		10.40	0.393		0.409
E1		8.50			0.334	
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.4	0.050		0.055
L3	1.40		1.75	0.055		0.068
М	2.40		3.2	0.094		0.126
R		0.40			0.016	
V2	0°		8°	0°		8°

# TO-263 (D<sup>2</sup>PAK) MECHANICAL DATA



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics. The ST logo is a trademark of STMicroelectronics

© 2001 STMicroelectronics - Printed in Italy - All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

57

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco -Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

http://www.st.com

6/6